

Figure 1 consists of two technical drawings of a transistor package. The top drawing is a side view of the collector, showing a cylindrical component with a central pin. Dimensions are given in inches and parentheses in millimeters: 0.40(0.016) for the base width, 2.50(0.099) for the main body length, 9.00(0.354) (2 P.L.S.) for the total length, 2.00(0.079) for the distance from the base to the main body, and 0.50(0.020) for the distance from the main body to the collector mark. A central pin is labeled with a diameter of $\phi 1.70(\pm 0.067)$. The bottom drawing is a side view of the emitter, showing a similar cylindrical component. Dimensions are: 1.50(0.056) (2 P.L.S.) for the base width, 1.40(0.055) for the main body length, and 2.45(0.096) for the total length. It also labels the anode, emitter, and collector terminals.

Ic (mA) @ EV ~ 1000 Lx				λ_p (nm) Typ	$\Delta \theta$ deg Typ	λ (nm)	tr/tf @ VEC 5V Ic 1mA
Min	Typ	Max	VCE (V)				
—	6.0	—	3.0	900	±20	600 ~ 1050	15/15 μ S

Ic (mA) @ EV ~ 1000 Lx				λ_p (nm) Typ	$\Delta \theta$ deg Typ	λ (nm)	tr/ff @ VEC 5V Ic 1mA
Min	Typ	Max	VCE (V)				
0.5	—	—	10.0	900	±60	600 ~ 1050	15/15 μ S

Ic (mA) @ EV ~ 1000 Lx				λ_p (nm) Typ	$\Delta \theta$ deg Typ	λ (nm)	tr/ff @ VEC 5V Ic 1mA
Min	Typ	Max	VCE (V)				
0.8	—	—	10.0	900	±60	600 ~ 1050	15/15 μ s

Ic (mA) @ EV ~ 1000 Lx				λ_p (nm) Typ	$\Delta \theta$ deg Typ	λ (nm)	tr/tf @ VEC 5V Ic 1mA
Min	Typ	Max	VCE (V)				
0.8	—	15	5.0	880	±25	500 ~ 1050	5/5 μ S